

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/810779	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 15:28
L2	3250	(insulat\$3 dielectric oxide) with (high near4 constant) same (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 17:45
L3	1278	2 and (insulat\$3 dielectric oxide) with (high near4 constant) same (substrate)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 15:31
L4	255	3 and (nanometer 'nm' angstrom micrometer) with (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 15:40
L5	19	3 and (dot quantum quantum near3 dot anti adj dot) with (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 15:47
L7	33	3 and (dot quantum quantum near3 dot anti adj dot island) with (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 15:50
L8	38	3 and (dot quantum quantum near3 dot anti adj dot island cluster) with (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 15:44
L9	197	3 and (nano\$7)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 15:44
L11	24	3 and (nano-\$10)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 15:52
L12	197	11 or 9	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 16:02

L14	1007	(insulat\$3 dielectric oxide) with (high near4 constant) with (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 17:28
L15	1	14 and (nano-\$10) with (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 17:29
L16	5	14 and (quantum) with (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 17:38
L17	143	14 and (nanometer nm ansgtrom "'u.m'") with (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 17:39
L18	0	14 and ("'u.m'") with (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 17:39
L19	143	14 and (nanometer nm ansgtrom) with (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 17:39
L20	5	(insulat\$3 dielectric oxide) with (high near4 constant) same (trench opening groove hole via recess) same quantum	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 17:48